N-Channel 120-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	Дþ	plica	atior	ıs:
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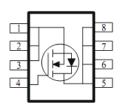
- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
120	21 @ V _{GS} = 10V	13		
120	24 @ V _{GS} = 4.5V	12		



FREE





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			120	V		
Gate-Source Voltage	V_{GS}	±20	V			
Continuous Drain Current ^a	T _A =25°C	L	13			
Continuous Drain Current		l _D	10	Α		
Pulsed Drain Current ^b	I _{DM}	50				
Continuous Source Current (Diode Conduction) a	I _S	6.7	Α			
Dower Dissipation a	T _A =25°C	P_{D}	5	W		
Power Dissipation ^a	T _A =70°C	' D	3.2	VV		
Operating Junction and Storage Temperature Range	T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State	IΛθJA	65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

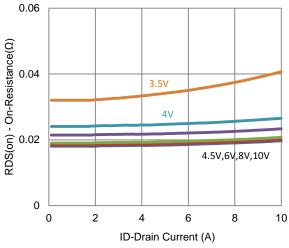
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 96 \text{ V}, V_{GS} = 0 \text{ V}$	50 1 00		uA		
Zero Gate Voltage Drain Gurrent	I _{DSS}	$V_{DS} = 96 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	T UA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Dania Carras On Basistana a	r	$V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$			21	mΩ	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$			24	11177	
Forward Transconductance a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$		28		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.4 \text{ A}, V_{GS} = 0 \text{ V}$		0.78		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 60 \text{ V}, V_{GS} = 4.5 \text{ V},$		52			
Gate-Source Charge	Q_{gs}	$V_{DS} = 00 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 10 \text{ A}$		19		nC	
Gate-Drain Charge	Q_gd	1D = 10 K		16			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 60 \text{ V}, R_{L} = 6 \Omega,$		23			
Rise Time	t _r	$V_{DS} = 60 \text{ V}, K_L - 6 \Omega,$ $I_D = 10 \text{ A},$		14		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		155		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		31			
Input Capacitance	C _{iss}			10696			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		239	_	pF	
Reverse Transfer Capacitance	C_{rss}			158			

Notes

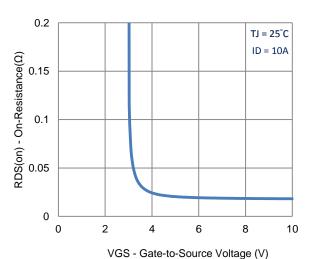
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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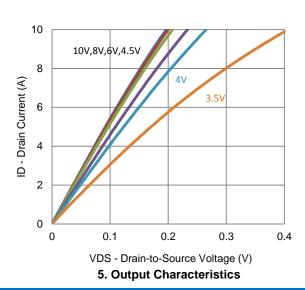
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



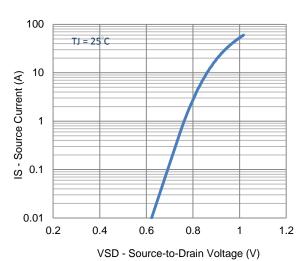
TJ = 25°C

(Y) 20

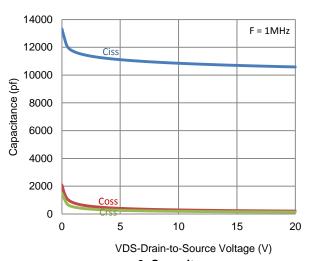
O 2 4 6 8

VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

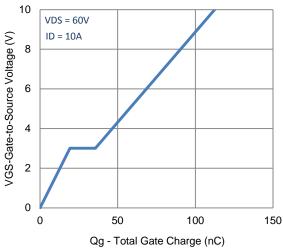


4. Drain-to-Source Forward Voltage

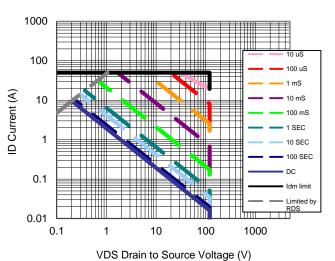


6. Capacitance

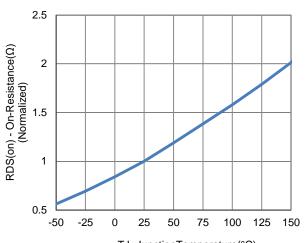
Typical Electrical Characteristics



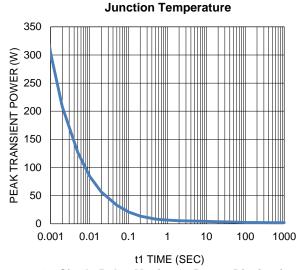
7. Gate Charge (nc)



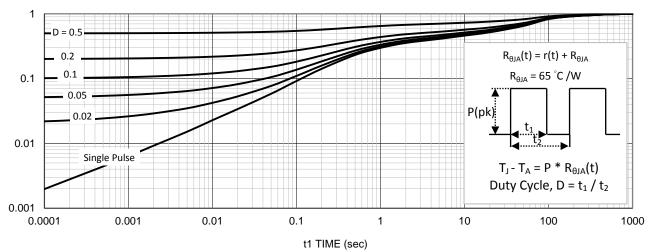
9. Safe Operating Area



TJ -JunctionTemperature(°C)
8. Normalized On-Resistance Vs

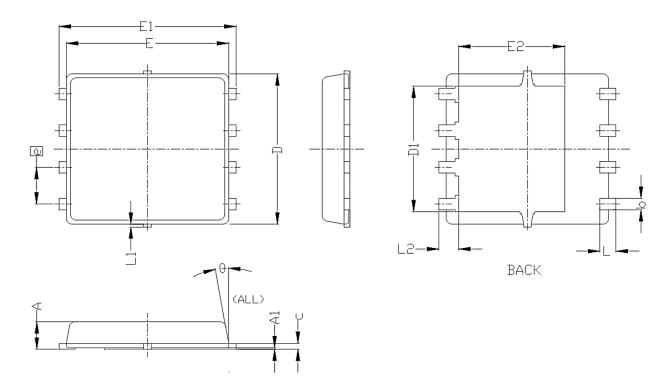


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0. 95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е		5, 55 BSC 0, 2			0.219 BSC		
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	